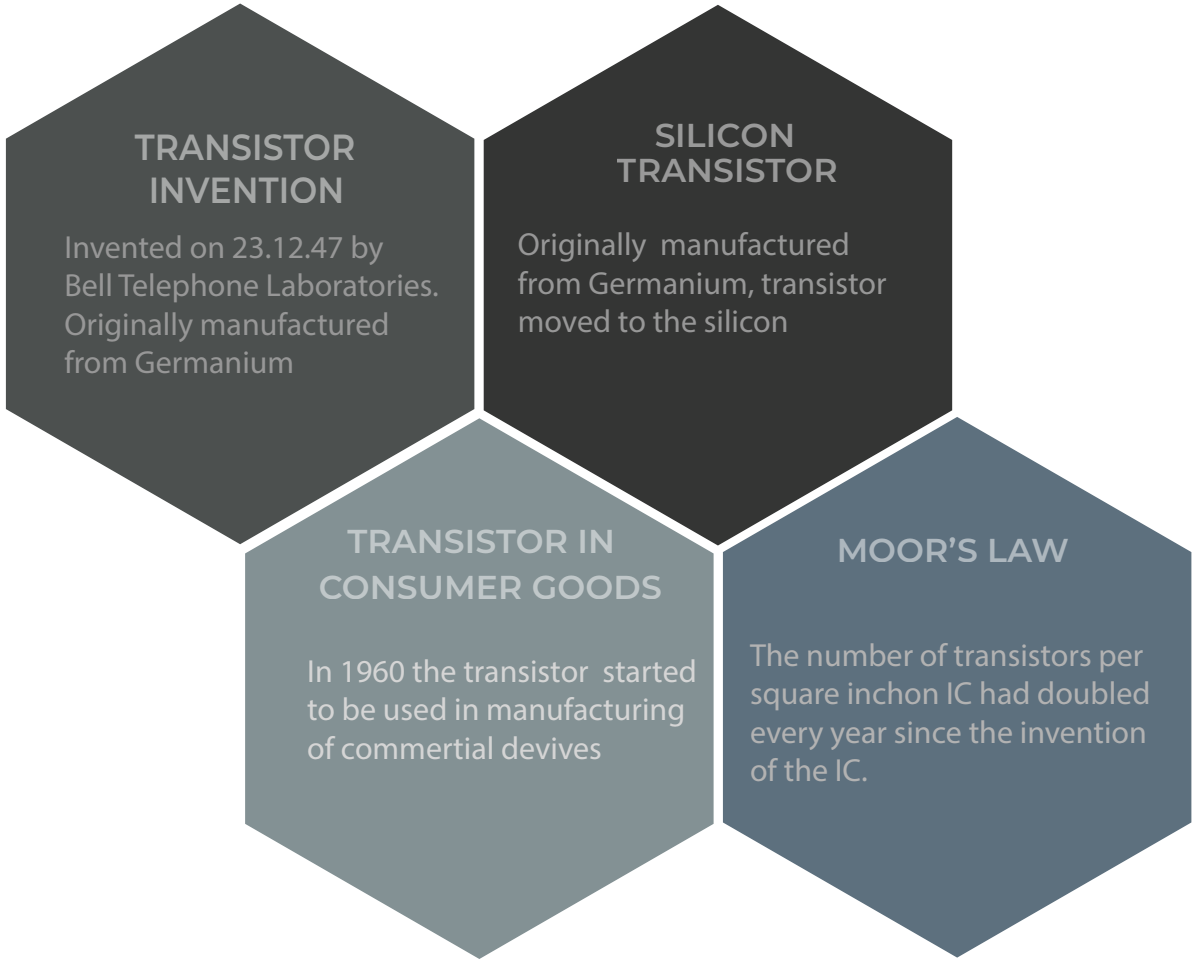


WHAT DO WE KNOW ABOUT TRANSISTORS?



THE TRANSISTOR IS A THREE-TERMINAL SEMICONDUCTOR DEVICE THAT CAN PERFORM SIGNAL SWITCHING AND AMPLIFYING

A BIPOLAR JUNCTION TRANSISTOR IS A SEMICONDUCTOR DEVICE BASED ON TWO P-N JUNCTIONS, CHARACTERISED WITH AN AMPLIFICATION FEATURE

- APPLICATIONS:**
- AMPLIFIERS
 - HIGH-SPEED DIGITAL LOGIC
 - TEMPERATURE SENSORS
 - CONVERTERS

$$\alpha = \frac{I_c}{I_e}$$

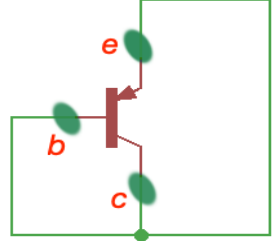
Amplification factor collector-emitter

Amplification factor collector-base

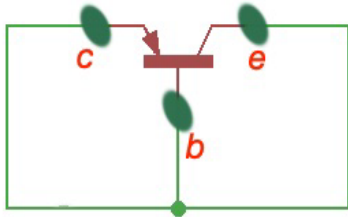
$$\beta = \frac{I_c}{I_b}$$

$$I_e = I_c + I_b$$

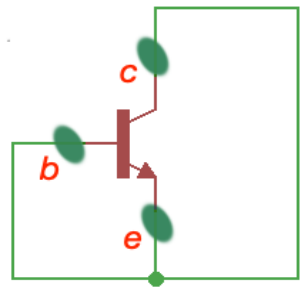
KL for BJT



Common-collector BJT configuration



Common-base BJT configuration



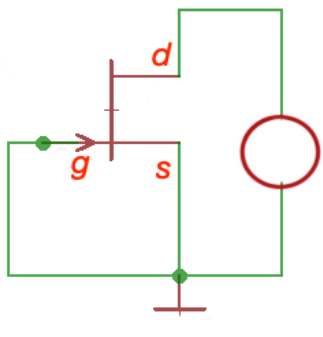
Common-emitter BJT configuration

A FIELD EFFECT TRANSISTOR IS A SEMICONDUCTOR DEVICE WHERE A GATE TERMINAL CAN BE MANIPULATED BY THE CHARGE FLOW ACROSS THE SEMICONDUCTOR CHANNEL BETWEEN DRAIN AND SOURCE

- FET TYPES:**
- JFET's use one-side p-n junction to separate body and gate
 - MOSFET's use insulator to separate body and gate
 - DG MOSFET is a MOSFET with two gates
 - TFET is a tunnelling FET
 - MESFET is a transistor that combines FET and diode Schottky

$$I_D = I_{DSS} \left(1 - \frac{v_{GS}}{v_p}\right)^2$$

$$v_{GS} = v_p \left(1 - \sqrt{\frac{I_D}{I_{DSS}}}\right)$$



FET configuration

MOSFET IS A FET EQUIPPED WITH FOUR TERMINALS, WITH BULK CONNECTED TO THE SOURCE

OHMIC OPERATION REGION

$$R_{DS} = \frac{v_{Th}^2}{2I_{DSS}(v_{GS} - v_{Th})} \quad i_{DS} = \frac{v_{DS}}{R_{DS}}$$

SATURATION REGION

$$i_D = \frac{I_{DSS}}{V_T^2} (v_{GS} - v_{Th})^2$$

- MOSFET TYPES:**
- Enhancement mode
 - Depletion mode